

	Type	L #	Hits	Search T xt	DBs	Tim Stamp
1	BRS	L1	17642	(threshold or channel\$3) near4 (implant\$6 or inplant\$6)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/21 14:47
2	BRS	L2	302428 0	WELL\$3	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/21 14:48
3	BRS	L3	13470	(STI or LOCOS or (shallow adj trench adj isolation))	USPAT	2004/05/21 14:48
4	BRS	L4	3094	((threshold or channel\$3) near4 (implant\$6 or inplant\$6)) same WELL\$3	USPAT	2004/05/21 14:48
5	BRS	L5	1810	((threshold or channel\$3) near4 (implant\$6 or inplant\$6)) and WELL\$3 and ((MOSFET or CMOS or BICMOS or (metal adj oxide adj semiconductor adj field adj effect adj transistor) or (complementary adj metal adj oxide adj semiconductor))) and ((STI or LOCOS or (shallow adj trench adj isolation)))	USPAT	2004/05/21 14:48
6	BRS	L6	916	((threshold or channel\$3) near4 (implant\$6 or inplant\$6)) same WELL\$3) and ((MOSFET or CMOS or BICMOS or (metal adj oxide adj semiconductor adj field adj effect adj transistor) or (complementary adj metal adj oxide adj semiconductor))) and ((STI or LOCOS or (shallow adj trench adj isolation)))	USPAT	2004/05/21 14:48

	Type	L #	Hits	S arch Text	DBs	Time Stamp
7	BRS	L7	652	WELL\$3 near8 bur\$4 near8 (implant\$6 or inplant\$6)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/21 14:48
8	BRS	L8	159935	(MOSFET or CMOS or BICMOS or (metal adj oxide adj semiconductor adj field adj effect adj transistor) or (complementary adj metal adj oxide adj semiconductor))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/21 14:48
9	BRS	L9	500269 3	after\$4 or subsequent\$4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/21 14:48
10	IS&R	L10	142	(438/225).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/21 14:49
11	BRS	L11	1020	(P near2 base) near8 (WELL\$3)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/21 14:49
12	IS&R	L26	0	("20020158283").PN.	USPAT	2004/05/21 14:49

	Type	L #	Hits	Search T xt	DBs	Time Stamp
13	BRS	L12	115	((threshold or channel\$3) near4 (implant\$6 or inplant\$6)) same WELL\$3 same ((MOSFET or CMOS or BICMOS or (metal adj oxide adj semiconductor adj field adj effect adj transistor) or (complementary adj metal adj oxide adj semiconductor))) same ((STI or LOCOS or (shallow adj trench adj isolation)))	USPAT	2004/05/21 14:49
14	BRS	L13	801	(((((threshold or channel\$3) near4 (implant\$6 or inplant\$6)) same WELL\$3) and ((MOSFET or CMOS or BICMOS or (metal adj oxide adj semiconductor adj field adj effect adj transistor) or (complementary adj metal adj oxide adj semiconductor))) and ((STI or LOCOS or (shallow adj trench adj isolation))) not (((threshold or channel\$3) near4 (implant\$6 or inplant\$6)) same WELL\$3 same ((MOSFET or CMOS or BICMOS or (metal adj oxide adj semiconductor adj field adj effect adj transistor) or (complementary adj metal adj oxide adj semiconductor))) same ((STI or LOCOS or (shallow adj trench adj isolation)))	USPAT	2004/05/21 14:50
15	BRS	L14	398	(WELL\$3 near8 bur\$4 near8 (implant\$6 or inplant\$6)) and ((MOSFET or CMOS or BICMOS or (metal adj oxide adj semiconductor adj field adj effect adj transistor) or (complementary adj metal adj oxide adj semiconductor)))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/21 14:50

	Typ	L #	Hits	Search Text	DBs	Tim Stamp
16	BRS	L15	341	((WELL\$3 near8 bur\$4 near8 (implant\$6 or inplant\$6)) and ((MOSFET or CMOS or BICMOS or (metal adj oxide adj semiconductor adj field adj effect adj transistor) or (complementary adj metal adj oxide adj semiconductor)))) and (after\$4 or subsequent\$4)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/21 14:50
17	IS&R	L16	277	(438/276).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/21 14:50
18	BRS	L17	152	((P near2 base) near8 (WELL\$3)) same (implant\$4 or inplant\$4)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/21 14:50
19	BRS	L18	123	((P near2 base) near8 (WELL\$3)) same (implant\$4 or inplant\$4)) and ((MOSFET or CMOS or BICMOS or (metal adj oxide adj semiconductor adj field adj effect adj transistor) or (complementary adj metal adj oxide adj semiconductor)))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/21 14:50
20	IS&R	L19	578	(438/199).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/21 14:51

	Type	L #	Hits	S arch Text	DBs	Tim Stamp
21	IS&R	L20	197	(438/153).CCLS..	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/21 14:51
22	IS&R	L21	36	(438/188).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/21 14:51
23	IS&R	L22	1	("5270265").PN.	USPAT	2004/05/21 14:51
24	IS&R	L23	747	(438/154).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/21 14:51
25	IS&R	L24	1	("6015757").PN.	USPAT	2004/05/21 14:51
26	IS&R	L25	1	("6440640").PN.	USPAT	2004/05/21 14:51
27	IS&R	L27	1	("20020158283").PN.	USPAT; US-PGP UB	2004/05/21 14:51
28	BRS	L28	1013	epitaxial same locos	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/21 14:51

	Type	L #	Hits	S arch T xt	DBs	Tim Stamp
29	BRS	L29	75	(halo or pocket) and 28	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/21 14:54
30	BRS	L30	1775	church.in.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/21 14:54
31	BRS	L31	14	locos and epitaxial and 30	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2004/05/21 14:55